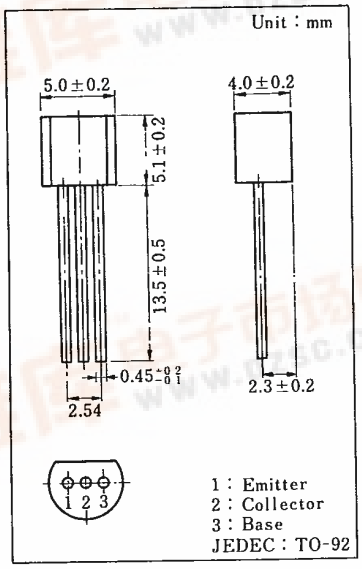
查询2SC2263供应商 捷多邦，专业PCB打样工厂，24小时加急出货

2SC2263

シリコン NPN エピタキシャルプレーナ形／Si NPN Epitaxial Planar

低周波低雑音増幅用／AF Low Noise Amplifier
2SA973とコンプリメンタリ／Complementary Pair with 2SA973



■ 特　徴／Features

- 雑音電圧 NV が低い。／Low NV
- ベース抵抗 r_{bb}' が低い。／Low r_{bb}'

■ 絶対最大定格／Absolute Maximum Ratings (Ta=25 ℃)

Item	Symbol	Value	Unit
コレクタ・ベース電圧	V_{CBO}	60	V
コレクタ・エミッタ電圧	V_{CEO}	55	V
エミッタ・ベース電圧	V_{EBO}	5	V
せん頭コレクタ電流	I_{CP}	100	mA
コレクタ電流	I_C	50	mA
コレクタ損失	P_C	400*	mW
接合部温度	T_j	150	℃
保存温度	T_{stg}	−55～+150	℃

* ポッティングタイプは P_C=250 mW／Potting type : P_C=250 mW

■ 電気的特性／Electrical Characteristics (Ta=25 ℃)

Item	Symbol	Condition	min.	typ.	max.	Unit
コレクタしゃ断電流	I_{CBO}	V_{CB}=30 V, I_E=0			100	nA
	I_{CEO}	V_{CE}=55 V, I_B=0			1	μA
コレクタ・ベース電圧	V_{CBO}	I_C=10 μA, I_E=0	60			V
コレクタ・エミッタ電圧	V_{CEO}	I_C=1 mA, I_B=0	55			V
エミッタ・ベース電圧	V_{EBO}	I_E=10 μA, I_C=0	5			V
直流電流増幅率	h_{FE}*	V_{CE}=5 V, I_C=2 mA	180		1040	
コレクタ・エミッタ飽和電圧	$V_{CE(sat)}$	I_C=10 mA, I_B=1 mA			0.6	V
ベース・エミッタ電圧	V_{BE}	V_{CE}=1 V, I_C=100 mA			1	V
ベース抵抗	r_{bb}'	V_{CB}=6 V, $-I_E$=1 mA, f=5 MHz		15		Ω
雑音電圧	NV	V_{CE}=40 V, I_C=1 mA, G_v=80 dB R_g=22 kΩ, Function=RIAA			150	mV

* h_{FE} ランク分類／h_{FE} Classifications

Class	R	S	T	U
h_{FE}	180～360	260～520	360～700	520～1040

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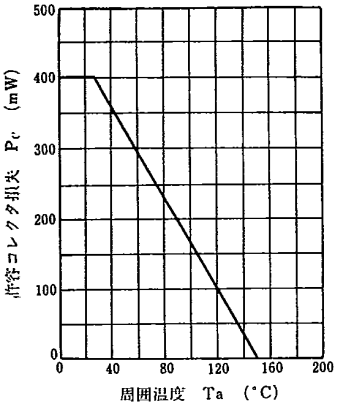
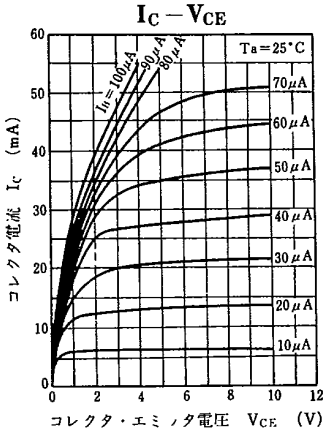
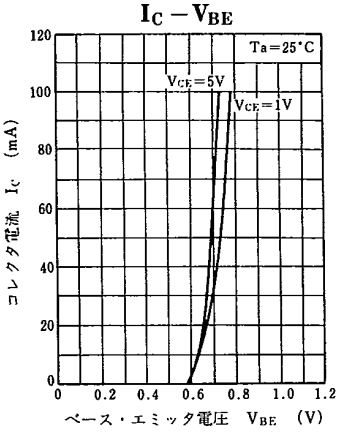
$P_C - Ta$



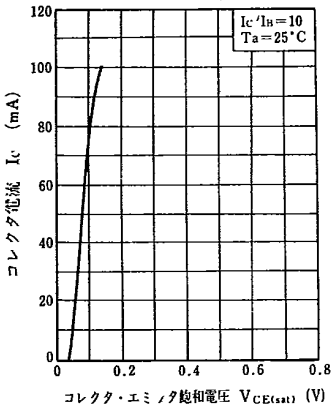
$I_C - V_{CE}$



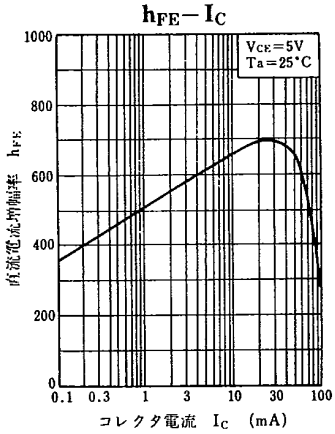
$I_C - V_{BE}$



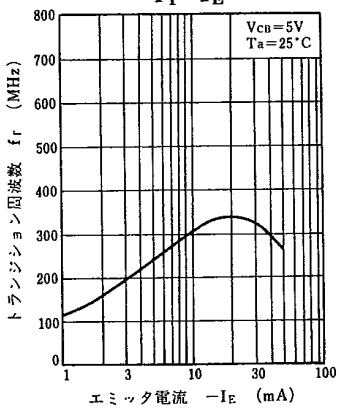
$I_C - V_{CE(sat)}$



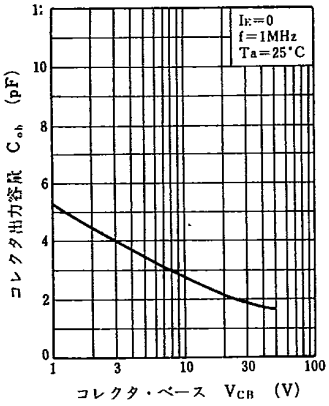
$h_{FE} - I_C$



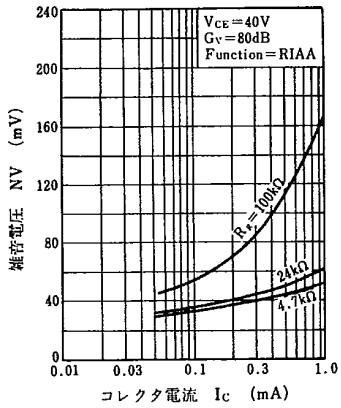
$f_T - I_E$



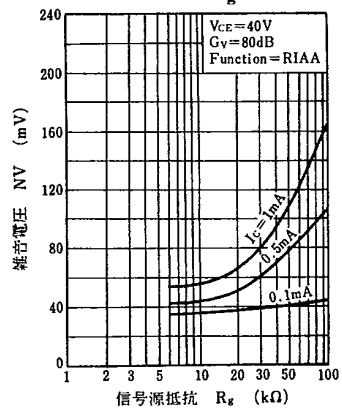
$C_{ob} - V_{CB}$



$NV - I_C$



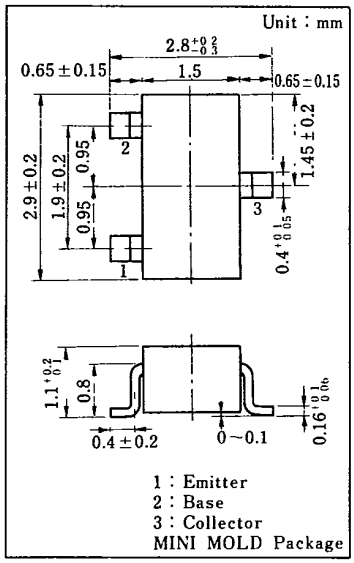
$NV - R_g$



2SC2295

シリコン NPN エピタキシャルプレーナ形／Si NPN Epitaxial Planar

高周波増幅用／RF Amplifier
2SA1022とコンプリメンタリ／Complementary Pair with 2SA1022



■ 特　徴／Features

- FM/AM ラジオの RF 増幅に最適です。／Suitable for RF amplifier in FM/AM radios
- トランジション周波数 f_T が高い。／High f_T

■ 絶対最大定格／Absolute Maximum Ratings (Ta=25 ℃)

Item	Symbol	Value	Unit
コレクタ・ベース電圧	V_{CBO}	30	V
コレクタ・エミッタ電圧	V_{CEO}	20	V
エミッタ・ベース電圧	V_{EBO}	5	V
コレクタ電流	I_C	30	mA
コレクタ損失	P_C	200	mW
接合部温度	T_j	125	℃
保存温度	T_{stg}	−55～+125	℃

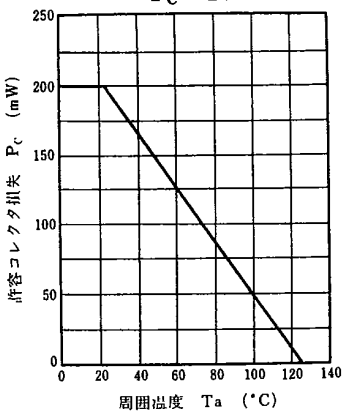
■ 電気的特性／Electrical Characteristics (Ta=25 ℃)

Item	Symbol	Condition	min.	typ.	max.	Unit
コレクタしゃ断電流	I_{CBO}	V_{CB}=10 V, I_E=0			0.1	μA
直流電流増幅率	h_{FE}*	V_{CB}=10 V, $-I_E$=1 mA	50		220	
トランジション周波数	f_T	V_{CB}=10 V, $-I_E$=1 mA	150			MHz
雑音指数	NF	V_{CB}=10 V, $-I_E$=1 mA, f=5 MHz		2.8	4	dB
帰還インピーダンス	Z_{rb}	V_{CB}=10 V, $-I_E$=1 mA, f=2 MHz		22	50	Ω
帰還容量	C_{re}	V_{CB}=10V, $-I_E$=1mA, f=10.7MHz		0.9	1.5	pF

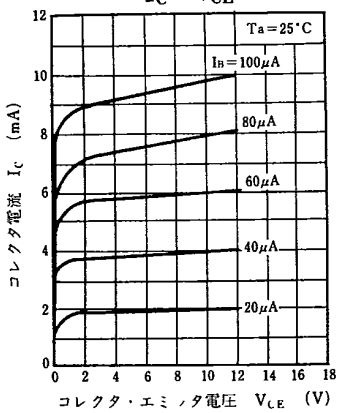
* h_{FE} ランク分類／h_{FE} Classifications

Class	A	B	C
h_{FE}	50～100	70～140	110～220
Marking Symbol	VA	VB	VC

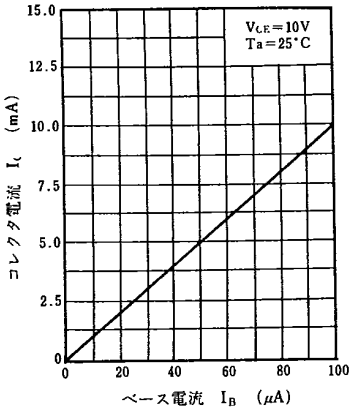
$P_C - Ta$



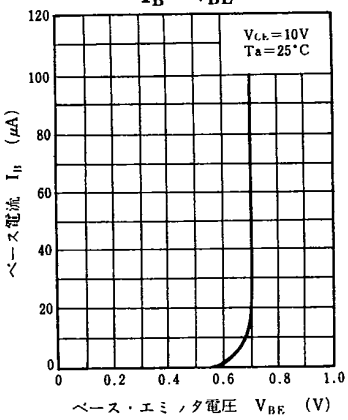
$I_C - V_{CE}$



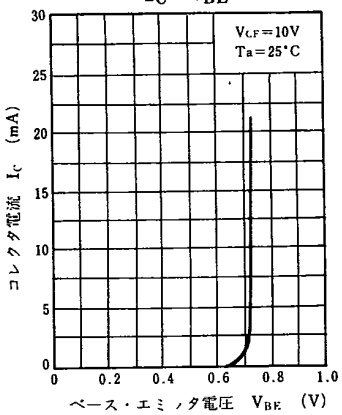
$I_C - I_B$



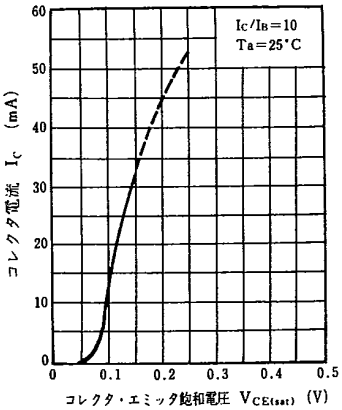
$I_B - V_{BE}$



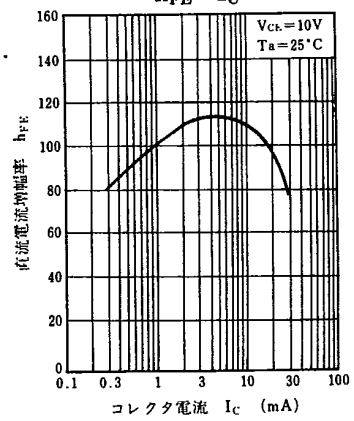
$I_C - V_{BE}$



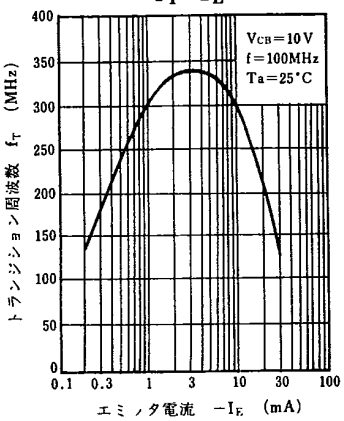
$I_C - V_{CE(sat)}$



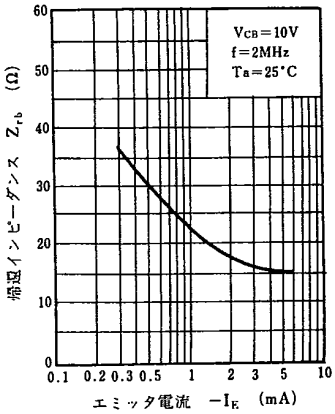
$h_{FE} - I_C$



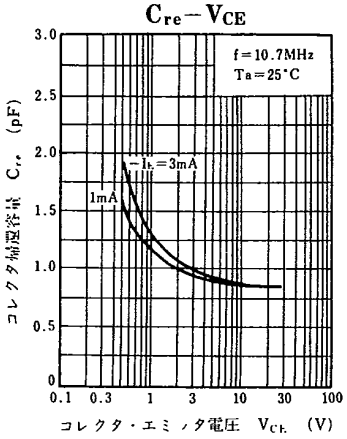
$f_T - I_E$



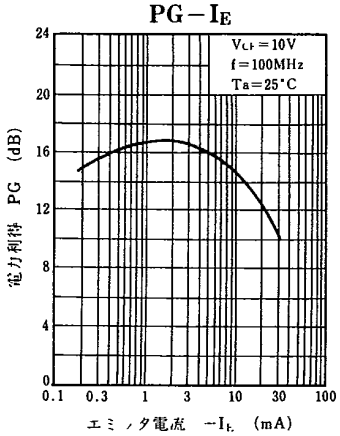
$Z_{rb} - I_E$



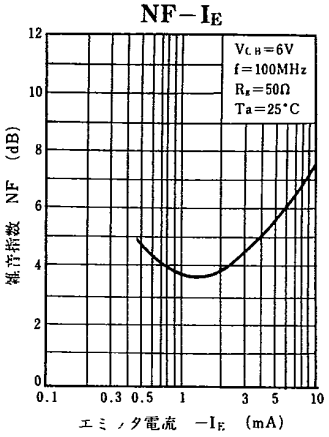
$C_{re}-V_{CE}$



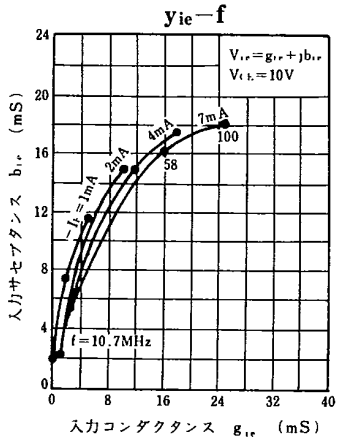
$PG-I_E$



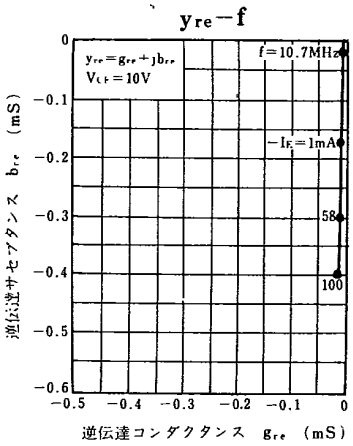
$NF-I_E$



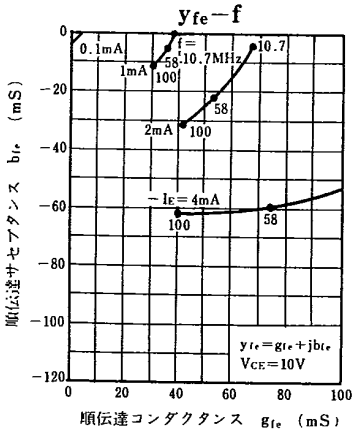
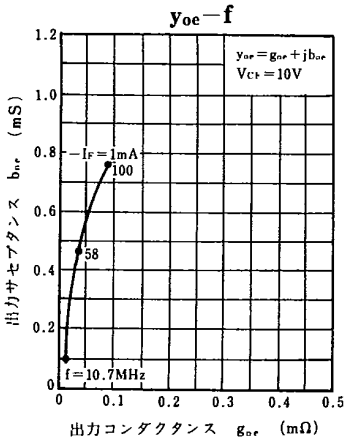
$y_{ie}-f$



$y_{re}-f$



$y_{fe}-f$



$y_{oe}-f$